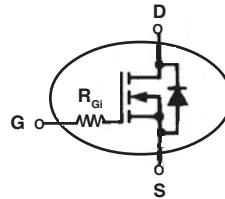
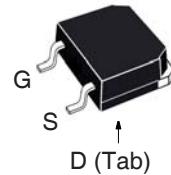
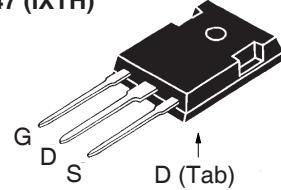


**LinearL2™
Power MOSFET
w/ Extended FBSOA**
**IXTT38N30L2HV
IXTH38N30L2**

V_{DSS} = 300V
 I_{D25} = 38A
 $R_{DS(on)}$ ≤ 100mΩ

N-Channel Enhancement Mode

TO-268HV (IXTT..HV)

TO-247 (IXTH)


G = Gate D = Drain
 S = Source Tab = Drain

Symbol	Test Conditions	Maximum Ratings		
V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	300		V
V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C , $R_{GS} = 1\text{M}\Omega$	300		V
V_{GSS}	Continuous	± 20		V
V_{GSM}	Transient	± 30		V
I_{D25}	$T_C = 25^\circ\text{C}$	38		A
I_{DM}	$T_C = 25^\circ\text{C}$, Pulse Width Limited by T_{JM}	120		A
I_A	$T_C = 25^\circ\text{C}$	38		A
E_{AS}	$T_C = 25^\circ\text{C}$	2.5		J
P_D	$T_C = 25^\circ\text{C}$	400		W
T_J		-55 ... +150		°C
T_{JM}		150		°C
T_{stg}		-55 ... +150		°C
T_L	Maximum Lead Temperature for Soldering	300		°C
T_{SOLD}	Plastic Body for 10s	260		°C
M_d	Mounting Torque (TO-247)	1.13 / 10	Nm/lb.in	
Weight	TO-268HV TO-247	4 6	g	g

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0\text{V}$, $I_D = 250\mu\text{A}$	300		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\mu\text{A}$	2.5		V
I_{GSS}	$V_{GS} = \pm 20\text{V}$, $V_{DS} = 0\text{V}$			±100 nA
I_{DSS}	$V_{DS} = V_{DSS}$, $V_{GS} = 0\text{V}$ $T_J = 125^\circ\text{C}$			10 μA 100 μA
$R_{DS(on)}$	$V_{GS} = 10\text{V}$, $I_D = 0.5 \cdot I_{D25}$, Note 1			100 mΩ

Features

- Designed for Linear Operation
- International Standard Packages
- Avalanche Rated
- Guaranteed FBSOA at 75°C

Advantages

- Easy to Mount
- Space Savings
- High Power Density

Applications

- Solid State Circuit Breakers
- Soft Start Controls
- Linear Amplifiers
- Programmable Loads
- Current Regulators

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$V_{DS} = 10\text{V}$, $I_D = 0.5 \cdot I_{D25}$, Note 1	12	16	20 S
C_{iss} C_{oss} C_{rss}	$V_{GS} = 0\text{V}$, $V_{DS} = 25\text{V}$, $f = 1\text{MHz}$	7200	pF	
		700	pF	
		200	pF	
R_{Gi}	Integrated Gate Input Resistor	3.4		Ω
$t_{d(on)}$ t_r $t_{d(off)}$ t_f	Resistive Switching Times $V_{GS} = 10\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 0.5 \cdot I_{D25}$ $R_G = 0\Omega$ (External)	30	ns	
		125	ns	
		94	ns	
		36	ns	
$Q_{g(on)}$ Q_{gs} Q_{gd}	$V_{GS} = 10\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 0.5 \cdot I_{D25}$	260	nC	
		43	nC	
		140	nC	
R_{thJC}			0.31 $^\circ\text{C}/\text{W}$	
R_{thCS}	TO-247	0.21		$^\circ\text{C}/\text{W}$

Safe Operating Area Specification

Symbol	Test Conditions	Characteristic Values		
		Min.	Typ.	Max.
SOA	$V_{DS} = 300\text{V}$, $I_D = 0.8\text{A}$, $T_c = 75^\circ\text{C}$, $T_p = 2\text{s}$	240		W

Source-Drain Diode

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max
I_s	$V_{GS} = 0\text{V}$		38	A
I_{SM}	Repetitive, pulse Width Limited by T_{JM}		152	A
V_{SD}	$I_F = I_s$, $V_{GS} = 0\text{V}$, Note 1		1.4	V
t_{rr} Q_{RM} I_{RM}	$I_F = 19\text{A}$, $-di/dt = 100\text{A}/\mu\text{s}$ $V_R = 100\text{V}$	420	ns	
		5.4	μC	
		27	A	

Note 1: Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.

PRELIMINARY TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: 4,835,592 4,931,844 5,049,961 5,237,481 6,162,665 6,404,065 B1 6,683,344 6,727,585 7,005,734 B2 7,157,338B2 4,860,072 5,017,508 5,063,307 5,381,025 6,259,123 B1 6,534,343 6,710,405 B2 6,759,692 7,063,975 B2 4,881,106 5,034,796 5,187,117 5,486,715 6,306,728 B1 6,583,505 6,710,463 6,771,478 B2 7,071,537

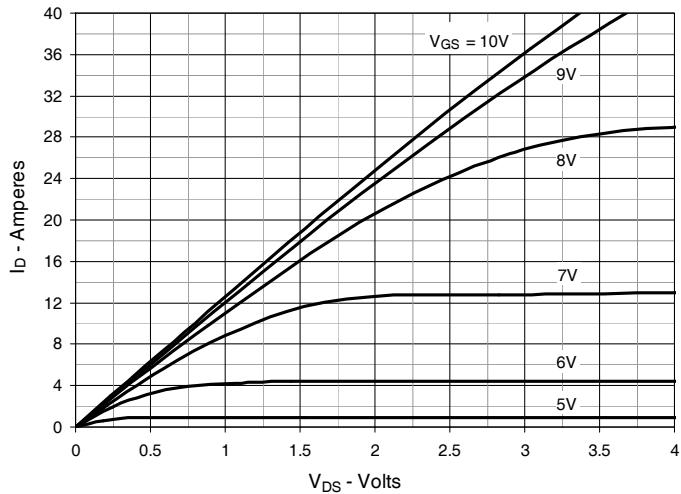
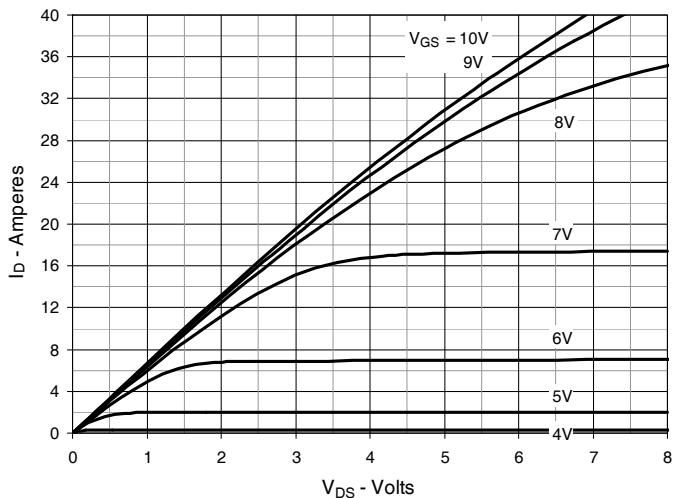
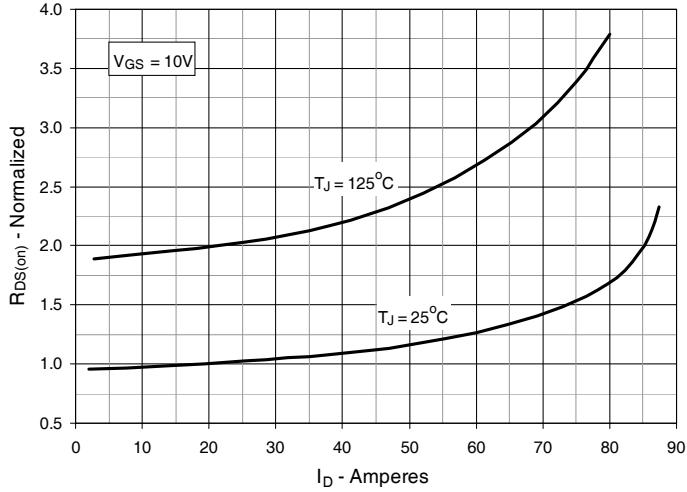
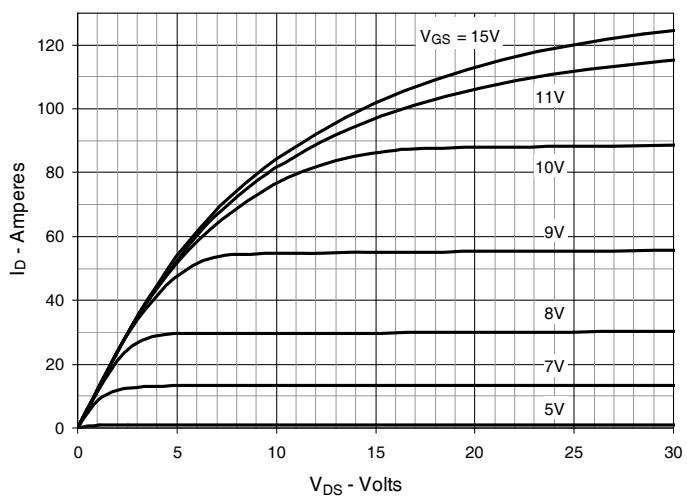
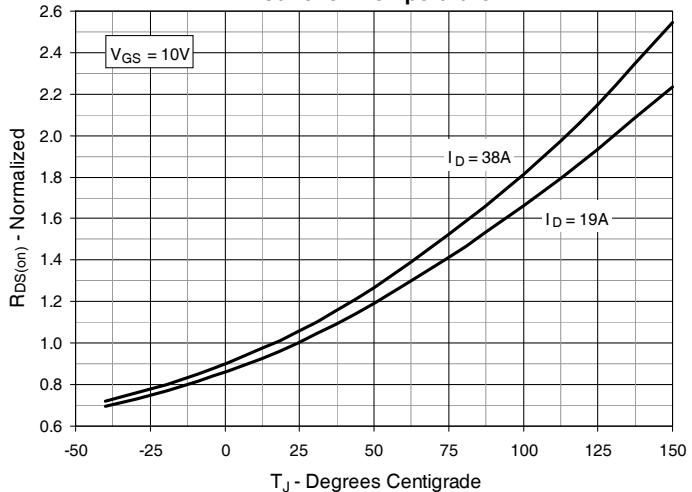
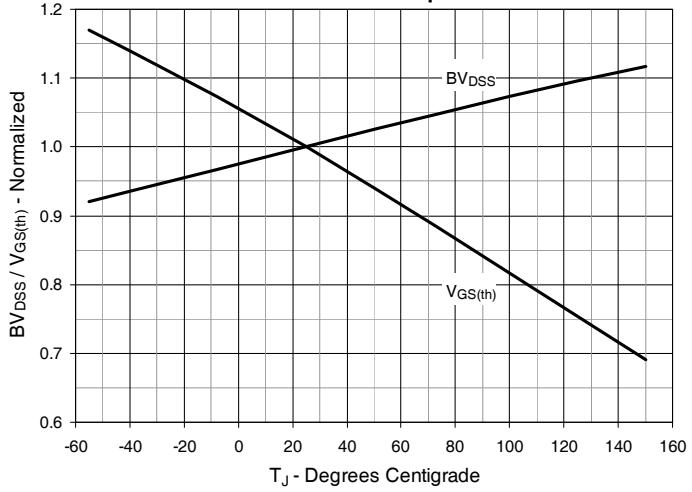
Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

Fig. 3. Output Characteristics @ $T_J = 125^\circ\text{C}$

Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 19\text{A}$ Value vs. Drain Current

Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 19\text{A}$ Value vs. Junction Temperature

Fig. 6. Normalized Breakdown & Threshold Voltages vs. Junction Temperature


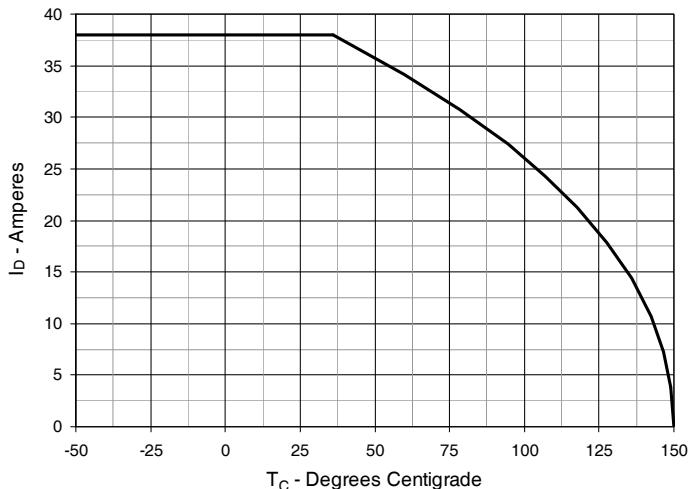
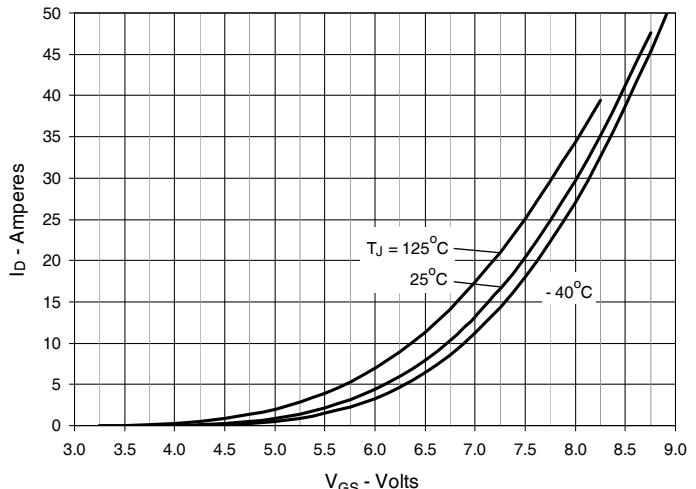
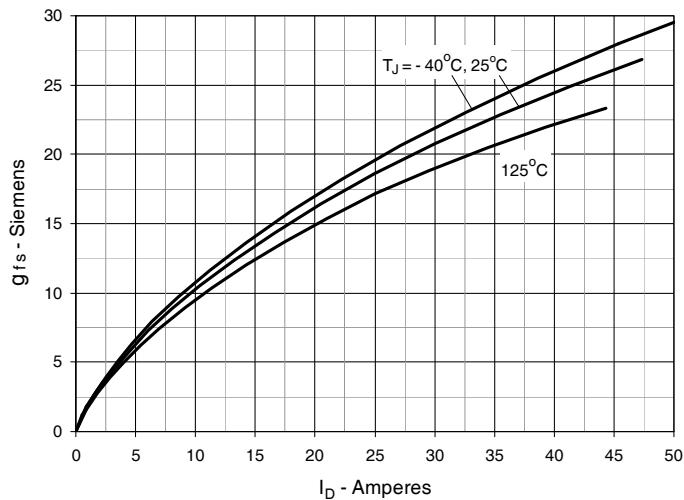
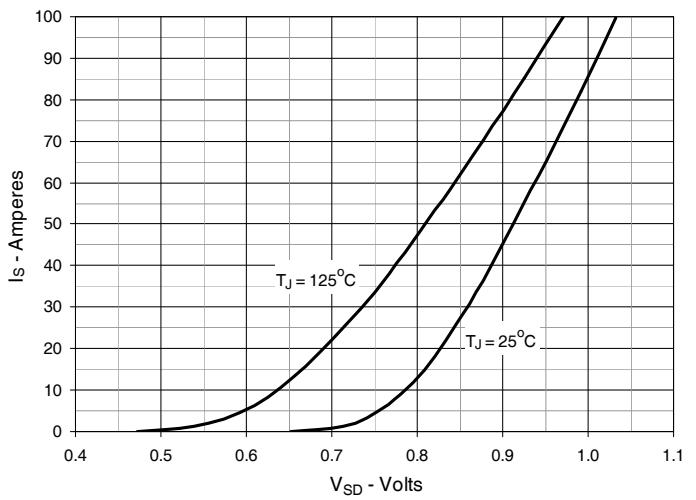
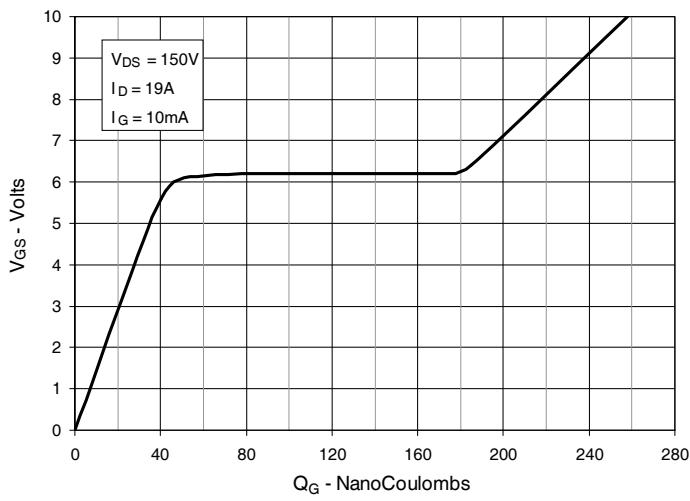
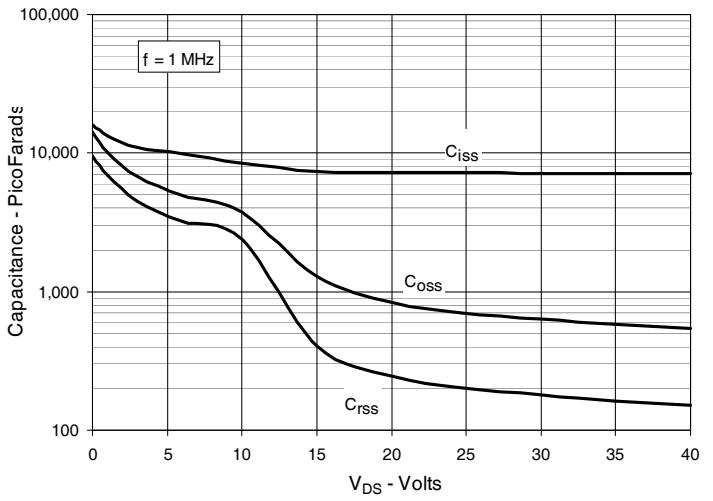
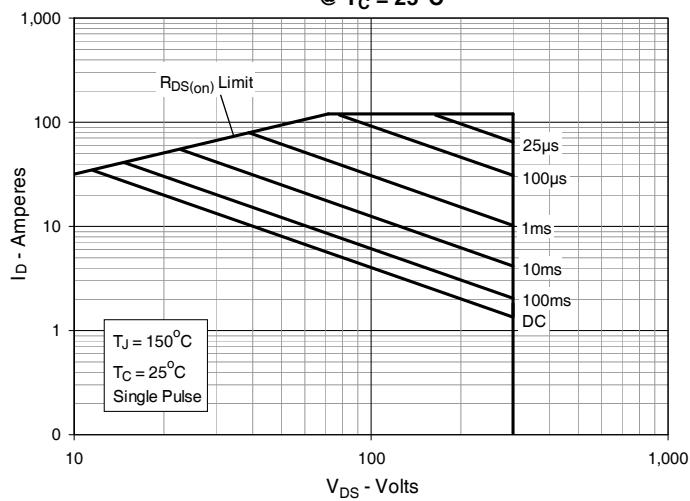
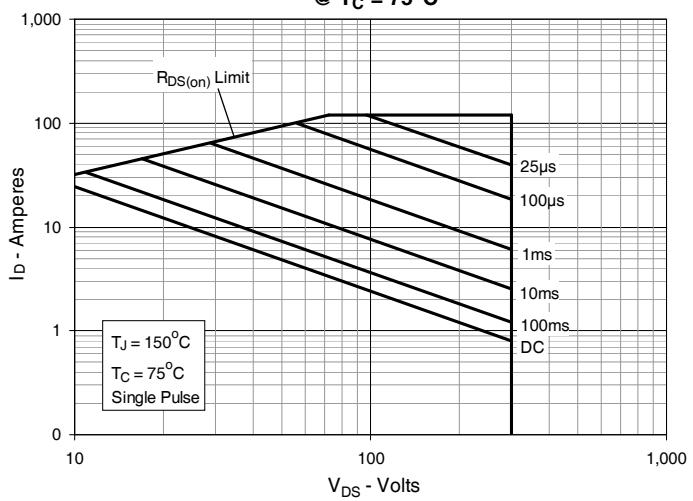
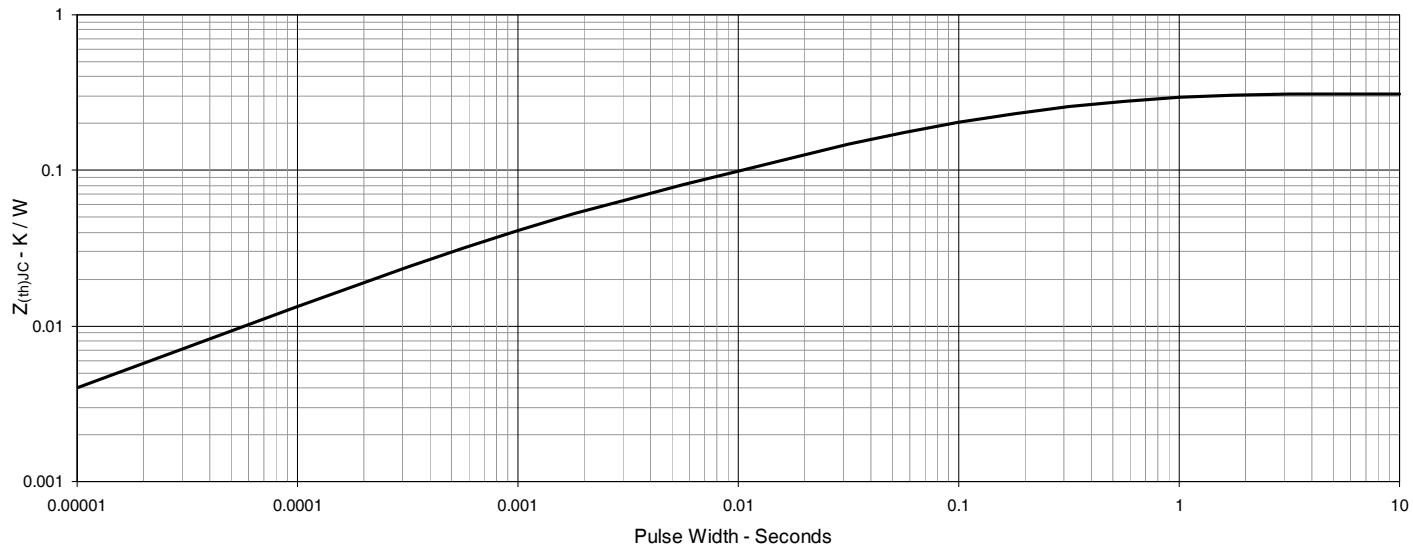
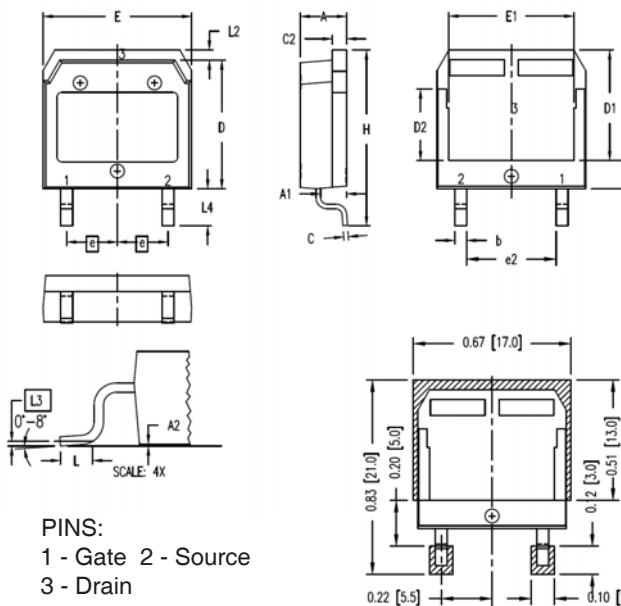
Fig. 7. Maximum Drain Current vs. Case Temperature

Fig. 8. Input Admittance

Fig. 9. Transconductance

Fig. 10. Forward Voltage Drop of Intrinsic Diode

Fig. 11. Gate Charge

Fig. 12. Capacitance


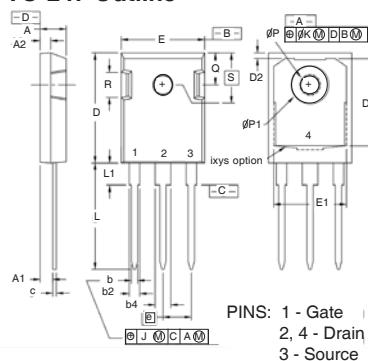
Fig. 13. Forward-Bias Safe Operating Area

@ $T_C = 25^\circ\text{C}$

Fig. 14. Forward-Bias Safe Operating Area

@ $T_C = 75^\circ\text{C}$

Fig. 15. Maximum Transient Thermal Impedance


TO-268HV Outline


SYM	INCHES		MILLIMETER	
	MIN	MAX	MIN	MAX
A	.193	.201	4.90	5.10
A1	.106	.114	2.70	2.90
A2	.001	.010	0.02	0.25
b	.045	.057	1.15	1.45
C	.016	.026	0.40	0.65
C2	.057	.063	1.45	1.60
D	.543	.551	13.80	14.00
D1	.465	.476	11.80	12.10
D2	.295	.307	7.50	7.80
D3	.114	.126	2.90	3.20
E	.624	.632	15.85	16.05
E1	.524	.535	13.30	13.60
(e)	.215	BSC	5.45	BSC
(e2)	.374	.386	9.50	9.80
H	.736	.752	18.70	19.10
L	.067	.079	1.70	2.00
L2	.039	.045	1.00	1.15
(L3)	.010	BSC	0.25	BSC
L4	.150	.161	3.80	4.10

TO-247 Outline


SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.190	.205	4.83	5.21
A1	.090	.100	2.29	2.54
A2	.075	.085	1.91	2.16
b	.045	.055	1.14	1.40
b2	.075	.087	1.91	2.20
b4	.115	.126	2.92	3.20
C	.024	.031	0.61	0.80
D	.819	.840	20.80	21.34
D1	.650	.690	16.51	17.53
D2	.035	.050	0.89	1.27
E	.620	.635	15.75	16.13
E1	.545	.565	13.84	14.35
e	.215	BSC	5.45	BSC
J	--	.010	--	0.25
K	--	.025	--	0.64
L	.780	.810	19.81	20.57
L1	.150	.170	3.81	4.32
ØP	.140	.144	3.55	3.65
ØP1	.275	.290	6.99	7.37
Q	.220	.244	5.59	6.20
R	.170	.190	4.32	4.83
S	.242	BSC	6.15	BSC